Bus Switch UT54BS3245 8-bit Bus Switch



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The most important thing we build is trust

FEATURES

- 3.3V operating power supply with typical 11Ω switch connection between ports
- 5.0V operating power supply with typical 5Ω switch connection between ports
- Bidirectional operation
- □ Ultra-low power CMOS technology
- □ ESD Rating HBM: 2000V, Class 2
- □ Signal Isolation: -60dB
- □ Channel Bandwidth (3dB): 500MHz
- □ Standard Microcircuit Drawing (SMD):
 - o **5962-15244**
 - QML Q and V compliant part
- Package Options: 20-Lead Flatpack

OPERATIONAL ENVIRONMENT

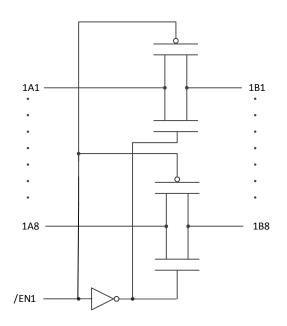
- □ Temperature Range: -55°C to +125°C
- □ Total Dose: 300 krad(Si)
- □ SEL Immune: ≤100 MeV-cm²/mg

APPLICATIONS

- □ Memory Interface
- Bus Isolation
- □ Redundancy
- Supports Analog Applications

INTRODUCTION

The UT54BS3245 provides 8 bits of high-speed CMOScompatible bus switching. The low on-state resistance of the switch allows connections to be made with minimal propagation delay. The device is organized as one 8-bit low-impedance switch. When output enable (/EN) is low, the 8-bit bus switch is on and port A is connected to port B. When /EN is high, the switch is open and a high-impedance state exists between the two ports.





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PINLIST

TO = TTL Output TTB = Three-State TTL Bidirectional CI = CMOS Input TUI = TTL Input (Internally Pulled High) TI = TTL Input TTO = Three-State TTL Output DIO = Differential Input/Output

Table 1: Pinlist					
NUMBER	NAME	DESCRIPTION			
2, 3, 4, 5, 6, 7, 8, 9,	nA	Port A Pins			
11, 12, 13, 14, 15, 16, 17, 18	nB	Port B pins			
19	/EN	Active LOW enable pin			
10	V _{SS}	Ground Pin			
20	V _{DD}	Supply Pin, +3.3V or +5.0V			
1	NC	No Connect (electrically not connected to die)			

PACKAGE PINOUT DIAGRAM

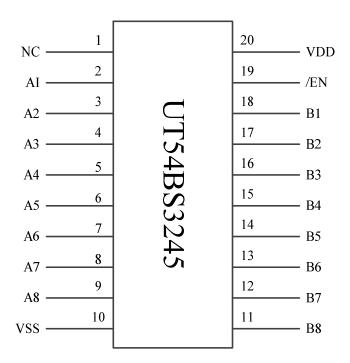


Figure 2: 8-bit Package Pinout Diagram

ABSOLUTE MAXIMUM RATINGS^{1, 2}

	Table 2: Absolute Maximum Ratings					
SYMBOL	PARAMETER	MIN	MAX	UNITS		
V _{DD}	Positive Supply Voltage	-0.5	+7.2	V		
VI	Input Voltage	-0.5	V _{DD} +0.3	V		
I _{CCC}	DC Channel Current		65	mA		
P _D	Max Power Dissipation ⁽³⁾		1.6	W		
Тյ	Junction Temperature		+150	°C		
θ_{JC}	Thermal resistance, junction-to-case		15	°C/W		
T _{STG}	Storage Temperature	-65	+150	°C		
ESD _{HBM}	ESD Protection ⁽⁴⁾		2000	V		

NOTE:

Stresses outside the listed absolute maximum ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond limits indicated in the operational sections of this specification are not recommended. Exposure to absolute maximum rating conditions for extended periods may affect device reliability and performance.

2. All voltages referenced to V_{SS}

3. Per MIL-STD-883, method 1012, section 3.4.1, $P_D = (T_J(max)-T_C(max))/\theta_{JC})$

4. Per MIL-STD-883, method 3015, Table 3

OPERATIONAL ENVIRONMENT⁽¹⁾

Table 3: Operational Environment

SYMBOL	PARAMETER	LIMIT	UNITS
TID	Total Ionizing Dose ⁽²⁾	300	krad(Si)
SEL	Single Event Latchup Immunity ⁽³⁾	≤100	MeV-cm ² /mg
NOTE			

NOTE:

1. For devices with procured with a total ionizing dose tolerance guarantee, post-irradiation performance is guaranteed at 25°C per MIL-STD-883 Method 1019, Condition A up to maximum TID level procured.

2. Per MIL-STD-883, method 1019, condition A

3. SEL is performed at VDD = Max Voltage at 125°C

RECOMMENDED OPERATING CONDITIONS⁽¹⁾

Table 4: Recommended Operating Conditions

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{DD}	Positive Supply Voltage	3.0 or 4.5	3.6 or 5.5	V
V _{IN}	Input Voltage on any pin	0.0	V_{DD}	V
T _C	Case Temperature Range	-55	+125	°C
t _R	Rise time	5		ns
t _F	Fall time	5		ns
I _{CCC}	DC Channel Current		60	mA

NOTE:

1. All voltages referenced to V_{SS}

DC ELECTRICAL CHARACTERISTICS⁽¹⁾ (V_{DD} = 5.0V ± 0.5V, 3.3V ± 0.3V, -55°C< T_c <+125°C); Unless otherwise noted, T_c is per the temperature range ordered Table 5: DC Electrical Characteristics

		Table 5: DC Electrical Characteristics			
SYMBOL	PARAMETER	CONDTIONS	MIN	MAX	UNITS
V_{IH}	High digital input voltage	V _{DD} = 3.6, 5.5	0.7* V _{DD}		V
V _{IL}	Low digital input voltage	V _{DD} = 3.0, 4.5		0.3* V _{DD}	V
I_{ID}	Leakage current digital	V_{DD} (max); $V_{I}=V_{DD}$ or V_{SS}	-1	1	μA
I_{IA}	Leakage current analog	V_{DD} (max); $V_{I}=V_{DD}$ or V_{SS}	-1	1	μA
I_{DD}	Active supply current	V _{DD} = 3.6, 5.5		0.1	mA/MHz
I_{DDQ}	Quiescent Supply Current	V _{DD} (max); I _O =0mA; /EN=V _{DD}		10	μA
CI	Input Capacitance (/EN) ⁽²⁾	$V_{I}=V_{DD}$ or V_{SS}		18	pF
C _{IO(OFF)}	Channel pin capacitance (channel disabled) ⁽²⁾	V_{DD} (max); $V_{O}=V_{DD}$ or V_{SS} ; $V_{I}=V_{DD}/2$; /EN= V_{DD}		18	pF
		V_{DD} =4.5V, V_{I} = V_{SS} , /EN=0V, I_{O} =30mA		10	Ω
D	Resistance through switch	V_{DD} =4.5V, V_{I} = V_{SS} , /EN=0V, I_{O} =15mA		10	Ω
R _{ONL}	(channel input low) ⁽³⁾	V_{DD} =3.0V, V_{I} = V_{SS} , /EN=0V, I_{O} =30mA		12	Ω
		V_{DD} =3.0V, V_{I} = V_{SS} , /EN=0V, I_{O} =15mA		12	Ω
		V_{DD} =4.5V, V_{I} = V_{DD} , /EN=0V, I_{O} =-30mA		10	Ω
р	Resistance through switch	V_{DD} =4.5V, V_{I} = V_{DD} , /EN=0V, I_{O} =-15mA		10	Ω
R _{ONH}	(channel input high) ⁽³⁾	V_{DD} =3.0V, V_{I} = V_{DD} , /EN=0V, I_{O} =-30mA		12	Ω
		V_{DD} =3.0V, V_{I} = V_{DD} , /EN=0V, I_{O} =-15mA		12	Ω
		V_{DD} =4.5V, /EN=0V, I_{O} = ^{+/-} 15mA, 25°C V_{IN} = V _{ss} , V _{DD} /2, V _{DD}		2	Ω
$R_{ON(FLAT)}$	Switch on resistance ⁽³⁾	V_{DD} =3.0V, /EN=0V, I_{O} =+/-15mA, 25°C V_{IN} = V _{ss} , V _{DD} /2, V _{DD}		10	Ω

NOTE:

All voltages referenced to V_{ss}
 Per MIL-STD-883, method 3012
 Guaranteed by Characterization

AC ELECTRICAL CHARACTERISTICS¹

 $(V_{DD}= 5.0V \pm 0.5V, 3.3V \pm 0.3V, -55^{\circ}C < T_{C} < +125^{\circ}C)$; Unless otherwise noted, T_{C} is per the temperature range ordered Table 6: AC Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNITS
t _{PD15}	Channel Propagation Delay ⁽¹⁾	V_{DD} = 5.0V ± 0.5V, I1=+/-15mA, /EN=V _{ss}		250	ps
t _{EN}	Channel Enable Delay ⁽²⁾	$V_{DD} = 5.0V \pm 0.5V$	1	5	ns
t _{DIS}	Channel Disable Delay ⁽²⁾	$V_{DD} = 5.0V \pm 0.5V$	1	5	ns
t _{PD15}	Channel Propagation Delay ⁽¹⁾	V_{DD} = 3.3V ± 0.3V, I1=+/-15mA, /EN=V _{ss}		250	ps
t _{EN}	Channel Enable Delay ⁽²⁾	$V_{DD} = 3.3V \pm 0.3V$	1	7	ns
t _{DIS}	Channel Disable Delay ⁽²⁾	$V_{DD} = 3.3V \pm 0.3V$	1	7	ns

NOTE:

1. The propagation delay through the channel is based on the RC time constant of the channel capacitance and maximum channel resistance for defined V_{DD}

2. Measured at 300mV above or below steady state output voltage using output test load circuit

		Table 7: Signal Characteristics				
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
X _{TALK} ¹	Channel Cross-Talk ^(1,2)	$V_{DD} = 5.0V$			-60	dB
X _{TALK} ¹	Channel Cross-Talk ^(1,2)	$V_{DD} = 3.3V$			-60	dB
ISO _{OFF} ¹	Off Isolation ^(1,2)				-60	dB
NOTE						

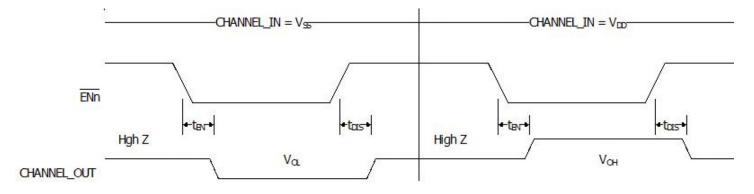
1. Guaranteed by design

2. RL = 50Ω , CL = 50pF, fin = 1MHz, Vin = 1VRMS centered at V_{DD}/2

TIMING DIAGRAM



Figure 3: Channel Propagations Delay (/EN = V_{SS})





TEST LOADS

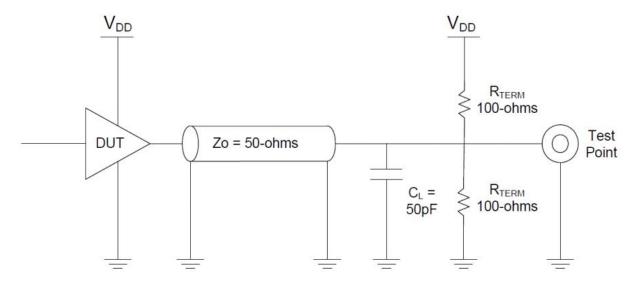


Figure 5: Standard Test Load

PACKAGE DRAWINGS

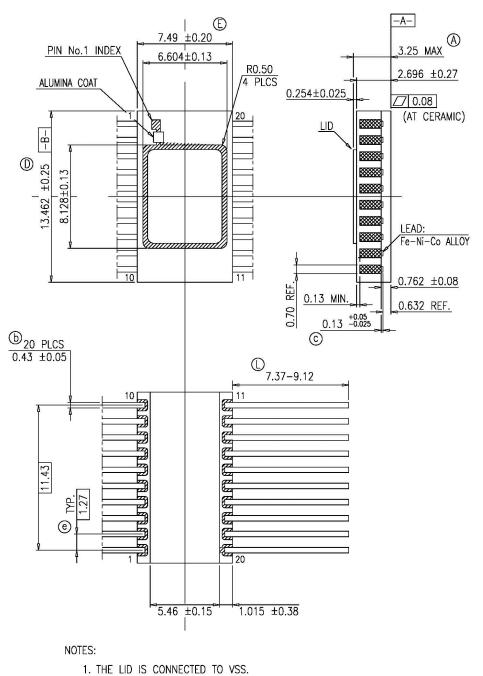
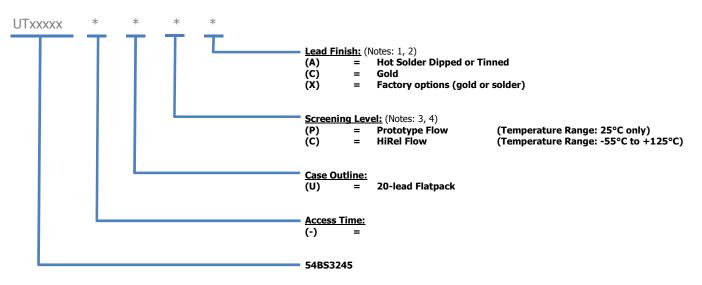


Figure 6: 20-Lead Flatpack

2. DIMENSIONS ARE IN MILLIMETERS.

ORDERING INFORMATION

Generic Datasheet Part Numbering

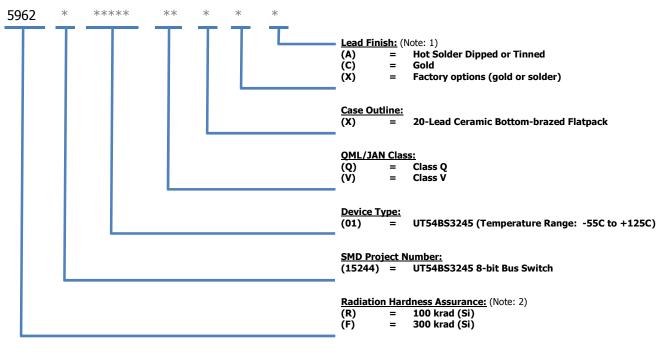


Notes:

- Lead finish (A, C, F, or X) must be specified.
 If an "X" is specified when ordering, then the part marking will match the lead finish applied to the device shipped
 Prototype Flow per Cobham Manufacturing Flows Document. Lead finish is Factory Option "C" only. Radiation is neither tested nor guaranteed.
 HiRel Flow per Cobham Manufacturing Flows Document. Radiation TID tolerance may (or may not) be ordered.

ORDERING INFORMATION

SMD Part Numbering



Federal Stock Class Designator

Notes:

Lead finish must be specified. If "X" is specified when ordering, the factory will determine lead finish. Part marking will reflect the lead finish applied to the device shipped.
 A radiation hardness assurance level must be selected. The use of "-" indicates no radiation hardness assurance guarantee.

REVISION HISTORY

NEVISION	111310		
		Table 8: Revision History	
Date	Rev. #	Change Description	Initials
05/01/2016	1.0.0	Updated datasheet to reflect Cobham logo, colors, and modified format. Updated the following specifications: R_{ON} , I_{IA} , I_{DD} , I_{DDO} , T_{EN} , and T_{DIS} .	ММ
06/23/2016	2.0.0	Released Datasheet. Updated capacitance, propagation delay, and minor formatting.	BM
6/30/2016	2.0.1	FEATURES: 20-Lead Flatpack; IDDQ: CONDITIONS: /EN=VDD	BM
01/04/2017	2.0.2	FEATURES: QML Q, V compliant part	BM

Template Revision: A

Cobham Semiconductor Solutions – Datasheet Definitions

Advanced Datasheet - Product In Development

Preliminary Datasheet - Shipping Prototype

Released Datasheet - Shipping QML & Reduced Hi – Rel

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